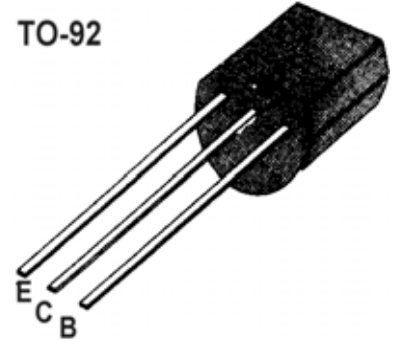


■■ APPLICATION: Medium Power Application.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	-80	V
Collector-emitter voltage	V _{CEO}	-80	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-700	mA
Collector Power Dissipation	P _C	1	W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

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■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	82		390		V _{CE} = -3V, I _C = -100mA
Collector Cut-off Current	I _{CBO}			-0.5	μA	V _{CB} = -50V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.5	μA	V _{EB} = -4V, I _C =0
Collector-Base Breakdown Voltage	BV _{CB0}	-80			V	I _C = -0.05mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-80			V	I _C = -2mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -0.05mA, I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.2	-0.4	V	I _C = -500mA, I _B = -50mA
Gain bandwidth product	f _T	50	100		MHz	I _C = -50mA, V _{CE} = -10V, f = 100MHz
Common Base Output Capacitance	C _{ob}		14	20	pF	V _{CB} = -10V, I _E =0, f = 1MHz

■■ h_{FE} Classification

Classification	P	Q	R
h _{FE}	82~180	120~270	180~390